

In the Specification:

Please replace the paragraph beginning at page 10, line 1, with the following paragraph:

FIGs. 6A and 6B illustrate an exemplary embodiment device isolation step for the FIGs. 3A – 3C formation method. FIG. 6A illustrates two transistor devices 8-29 formed in accordance with FIGs. 3A – 3C. The transistor devices 8 are formed as part of a single integration. In FIG. 6B laser irradiation 52 is tuned and controlled to ablate layers down to the substrate 34. The laser radiation may be varied in intensity or wavelength during the ablation of multiple layers. The ablation thereby creates a device isolation 54. In FIG. 6B, the device isolation takes the form of a gap. The gap may also be filled with isolation material, such as dielectric solution-processed thin film material. FIG. 7 illustrates a device isolation step for two transistor devices 48 formed in accordance with FIGs. 4A – 4C. In the exemplary embodiment of FIG. 7, the laser irradiation is tuned and controlled to form a device isolation 56 through the semiconductor layer up to the dielectric solution-processed thin film material layer 44. An optical mask may be used to create multiple features simultaneously, such as multiple device isolations 56. As in FIGs. 6A and 6B, the device isolation takes the form of a gap and also may be filled with isolation material.